



DMN3732UFB4Q

Product Summary

BV _{DSS}	Rds(on)	ID T _A = +25°C
30V	460mΩ @ V _{GS} = 4.5V	1.3A
300	560mΩ @ V _{GS} = 2.5V	1.2A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load switches
- Portable applications
- Power management functions

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- 0.4mm Ultra Low Profile Package for Thin Application
- 0.6mm² Package Footprint, 10 Times Smaller than SOT23
- Low VGS(TH), Can Be Driven Directly from A Battery
- Low RDS(ON)
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES[™] DMN3732UFB4Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

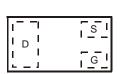
https://www.diodes.com/quality/product-definitions/

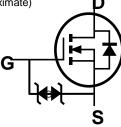
Mechanical Data

- Package: X2-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)









ESD PROTECTED

Equivalent Circuit

X2-DFN1006-3

Ordering Information (Note 4)

Part Number	Package Marking Reel Size (Inches) Tape Width (mn		Tana Width (mm)	Width (mm) Tape Pitch (mm)		Packing	
Fait Number			Tape width (mm)	Tape Fitch (IIIII)	Qty.	Carrier	
DMN3732UFB4Q-7B	X2-DFN1006-3	BF	7	8	2	10,000	Reel

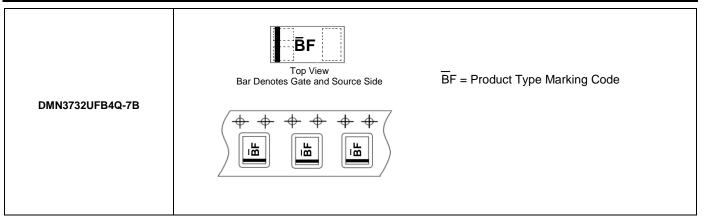
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			VDSS	30	V	
Gate-Source Voltage			Vgss	±8		
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	Steady State	T _A = +25°C T _A = +70°C	lo	1.3 1.1	A	
Maximum Continuous Body Diode Forward Current (Note 6)			ls	1.1	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			ldм	3.3	A	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.49	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	253	°C/W
Total Power Dissipation (Note 6)	· · · · · · · · · · · · · · · · · · ·	PD	1.12	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	112	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

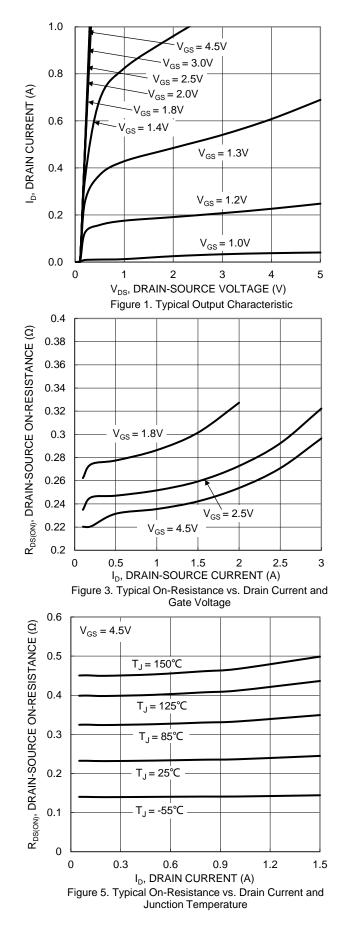
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

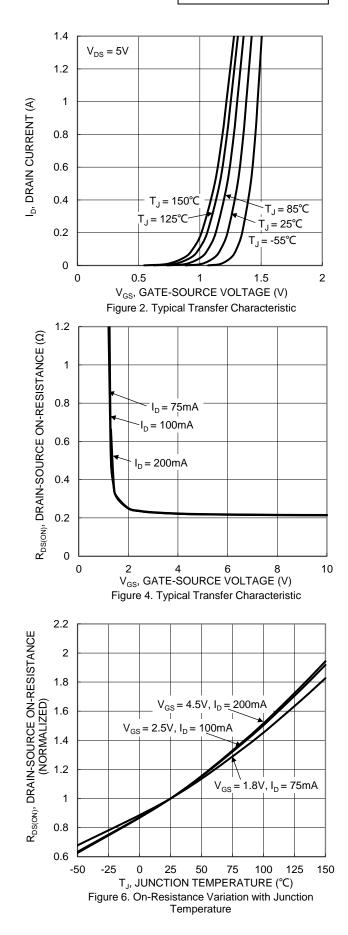
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_		±3	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(th)	0.45		0.95	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
		_	230	460		V _{GS} = 4.5V, I _D = 200mA
Static Drain-Source On-Resistance	RDS(ON)	_	250	560	mΩ	V _{GS} = 2.5V, I _D = 100mA
		_	278	730		V _{GS} = 1.8V, I _D = 75mA
Diode Forward Voltage	Vsd		0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	—	40.8	_	pF	
Output Capacitance	Coss	_	7.6	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	4.6	_	pF	
Total Gate Charge	Qg	_	0.9	—	nC	
Gate-Source Charge	Q _{gs}	_	0.05	—	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$
Gate-Drain Charge	Q _{gd}	_	0.3		nC	$-I_D = 1A$
Turn-On Delay Time	tD(ON)	_	1.1		ns	
Turn-On Rise Time	t _R	—	15.9	—	ns	$V_{DS} = 10V, I_D = 1A$
Turn-Off Delay Time	tD(OFF)	_	20.7	—	ns	$V_{GS} = 10V, R_G = 6\Omega$
Turn-Off Fall Time	t _F	_	20.0	—	ns	
Reverse Recovery Time	trr	_	59	—	ns	IF = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Qrr	_	25		nC	IF = 1A, di/dt = 100A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing. Notes:



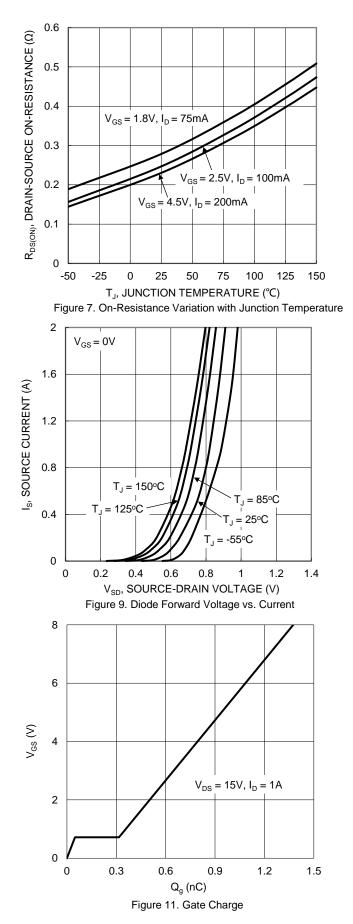
DMN3732UFB4Q

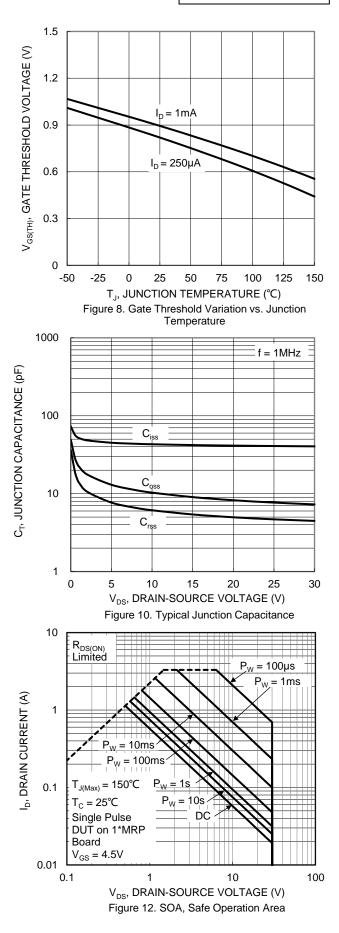




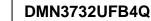


DMN3732UFB4Q





DMN3732UFB4Q Document number: DS45080 Rev. 2 - 2





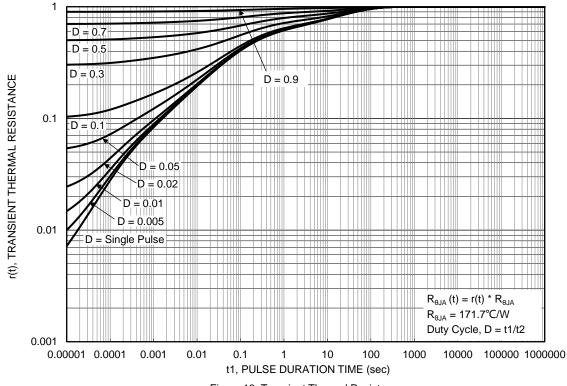


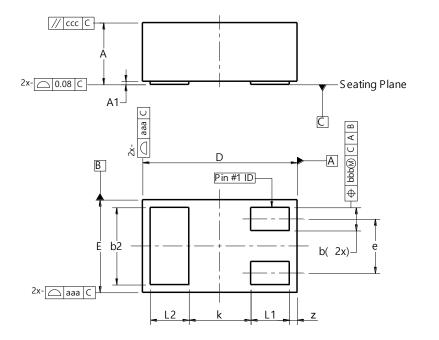
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

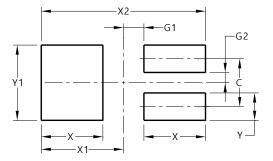


Х	X2-DFN1006-3					
Dim	Min	Max	Тур			
Α		0.40				
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.05	1.00			
Е	0.55	0.65	0.60			
е	-	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
k	-	-	0.40			
Z	0.02	0.08	0.05			
aaa	0.15					
bbb	0.05					
CCC	0.05					
All D	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
С	0.350
G1	0.150
G2	0.075
Х	0.450
X1	0.600
X2	1.200
Y	0.200
Y1	0.550



IMPORTANT NOTICE

1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

5 Diodes' provided to Diodes' Standard Terms and Conditions of Sale products are subject (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

DIODES is a trademark of Diodes Incorporated in the United States and other countries. The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. © 2022 Diodes Incorporated. All Rights Reserved.

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Diodes Incorporated manufacturer:

Other Similar products are found below :

 004419CB
 069117AB
 1.5KE15A-T
 1.5KE15CA-T
 1.5KE200A-T
 1.5KE20CA-T
 1.5KE27CA-T
 1.5KE30A-T
 1.5KE30A-T

 1.5KE33A-T
 1.5KE350A-T
 1.5KE36CA-T
 1.5KE47A-T
 1.5KE47CA-T
 1.5KE51CA-T
 1.5KE62A-T
 1.5KE68A-T
 1.5KE68CA

 1.5KE6V8CA-T
 1.5KE7V5A-T
 1.5KE82CA-T
 1.5KE9V1A-T
 1N4001G-T
 1N4002
 1N4002G-T
 1N4002-T
 1N4003G-T

 1N4003-T
 1N4004
 1N4004G-T
 1N4005-B
 1N4005G-T
 1N4005-T
 1N4006-B
 1N4006G-T
 1N4006-T
 1N4007G-T

 1N4007-T
 1N4148W-13-F
 1N4148W-7-F
 1N4148WQ-13-F
 1N4148WS-13-F
 1N4148WS-7-F
 1N4148WQ-7-F
 1N4148WS-13-F
 1N4148WS-7-F